



A Product Line of  
Diodes Incorporated



## ZXTP03200BG 200V PNP Low $V_{CE(sat)}$ transistor in SOT223

### Summary

$BV_{CEO} > -200V$

$BV_{ECO} > -2V$

$I_{C(cont)} = 2A$

$V_{CE(sat)} < -160mV @ -1A$

$R_{CE(sat)} = 135m\Omega$

$P_D = 3W$

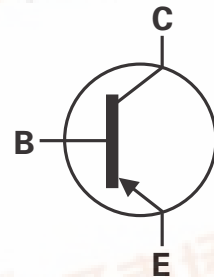


### Description

Packaged in the SOT223 outline this new 5<sup>th</sup> generation low saturation 200V PNP transistor offers extremely low on state losses making it ideal for use in DC-DC circuits and various driving and power management functions

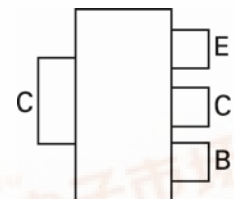
### Features

- 2 Amps continuous current
- Up to 5 Amps peak current
- Very low saturation voltage
- Enhanced switching performance



### Applications

- DC-DC conversion



Pin out - top view

### Ordering Information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP03200BGTA	7	12	1000

### Device Marking

ZXTP03200BG

# ZXTP03200BG

## Absolute Maximum Ratings

Parameter	Symbol	Limit	Unit
Collector-Base Voltage	$V_{CBO}$	-220	V
Collector-Emitter Voltage	$V_{CEO}$	-200	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current <sup>(a)</sup>	$I_C$	-2	A
Base Current	$I_B$	-1	A
Peak Pulse Current	$I_{CM}$	-5	A
Power Dissipation at $T_A=25^{\circ}\text{C}$ <sup>(a)</sup> Linear Derating Factor	$P_D$	1.25 10	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ <sup>(b)</sup> Linear Derating Factor	$P_D$	1.65 13.2	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ <sup>(c)</sup> Linear Derating Factor	$P_D$	3 24	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_A=25^{\circ}\text{C}$ <sup>(d)</sup> Linear Derating Factor	$P_D$	5.8 46.5	W mW/ $^{\circ}\text{C}$
Power Dissipation at $T_C=25^{\circ}\text{C}$ <sup>(e)</sup> Linear Derating Factor	$P_D$	11.9 95.2	W mW/ $^{\circ}\text{C}$
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to 150	$^{\circ}\text{C}$

## Thermal Resistance

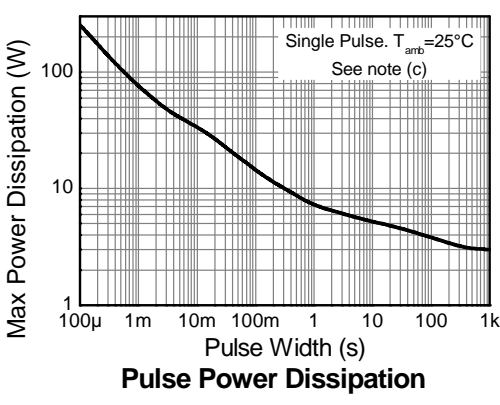
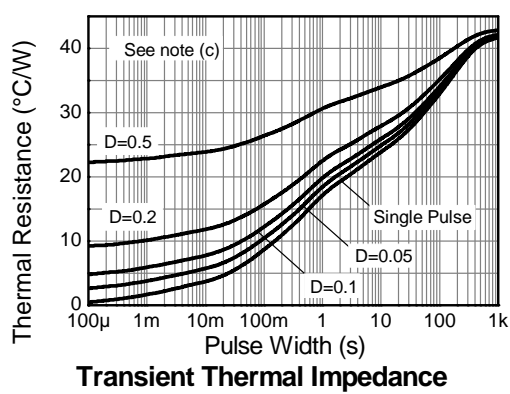
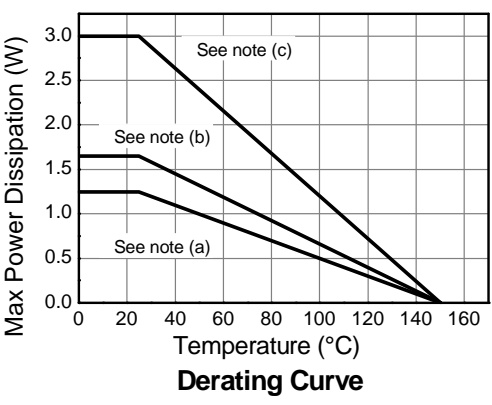
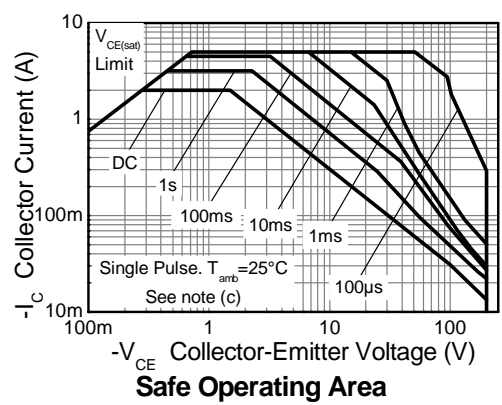
Parameter	Symbol	Value	Unit
Junction to Ambient <sup>(a)</sup>	$R_{\theta JA}$	100	$^{\circ}\text{C}/\text{W}$
Junction to Ambient <sup>(b)</sup>	$R_{\theta JA}$	76	$^{\circ}\text{C}/\text{W}$
Junction to Ambient <sup>(c)</sup>	$R_{\theta JA}$	41.6	$^{\circ}\text{C}/\text{W}$
Junction to Ambient <sup>(d)</sup>	$R_{\theta JA}$	21.5	$^{\circ}\text{C}/\text{W}$
Junction to Lead <sup>(e)</sup>	$R_{\theta JL}$	10.5	$^{\circ}\text{C}/\text{W}$

### NOTES:

- (a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.
- (d) As (c) above measured at  $t < 5$  seconds.
- (e) Junction to Lead from Collector Tab. Typical

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## Thermal Characteristics



# ZXTP03200BG

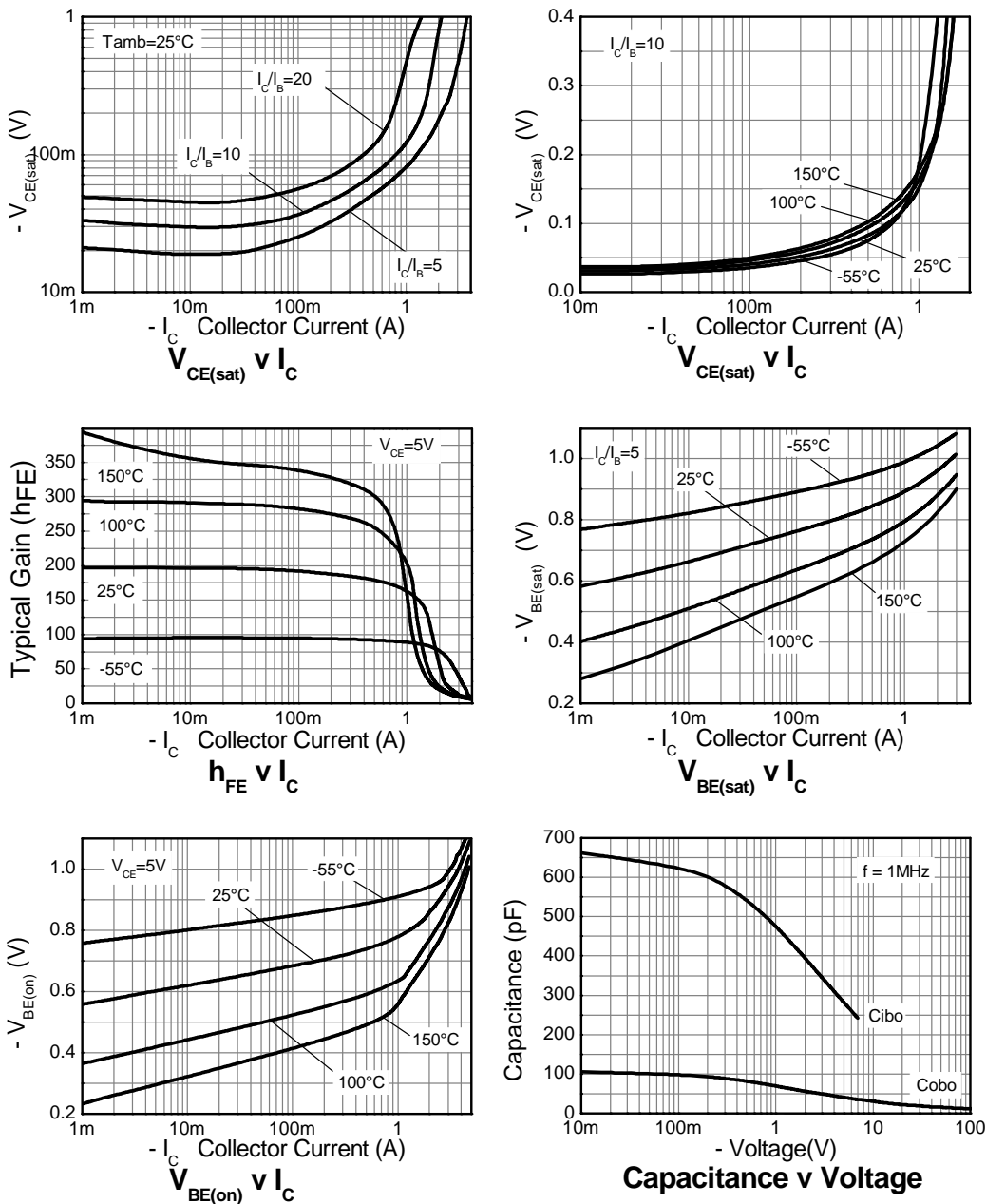
## Electrical Characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-Base Breakdown Voltage	$BV_{CBO}$	-220	-245		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$BV_{CER}$	-220	-245		V	$I_C = -1\mu\text{A}$ , $R_{BE} \leq 1\text{k}\Omega$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	-200	-225		V	$I_C = -10\text{mA}$ (*)
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.4		V	$I_E = -100\mu\text{A}$
Collector-Base Cut-off Current	$I_{CBO}$		<1	-50 -0.5	nA $\mu\text{A}$	$V_{CB} = -200\text{V}$ $V_{CB} = -200\text{V}$ , $T_{amb} = 100^{\circ}\text{C}$
Emitter Cut-off Current	$I_{EBO}$		<1	-10	nA	$V_{EB} = -6\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-37	-50	mV	$I_C = -0.1\text{A}$ , $I_B = -10\text{mA}$ (*)
			-130	-155	mV	$I_C = -0.5\text{A}$ , $I_B = -25\text{mA}$ (*)
			-135	-160	mV	$I_C = -1\text{A}$ , $I_B = -100\text{mA}$ (*)
			-180	-275	mV	$I_C = -2\text{A}$ , $I_B = -400\text{mA}$ (*)
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-955	-1100	mV	$I_C = -2\text{A}$ , $I_B = -400\text{mA}$ (*)
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-860	-1000	mV	$I_C = -2\text{A}$ , $V_{CE} = -5\text{V}$ (*)
Static Forward Current Transfer Ratio	$h_{FE}$	100	195			$I_C = -10\text{mA}$ , $V_{CE} = -5\text{V}$ (*)
		100	170	300		$I_C = -1\text{A}$ , $V_{CE} = -5\text{V}$ (*)
		20	50			$I_C = -2\text{A}$ , $V_{CE} = -5\text{V}$ (*)
			5			$I_C = -5\text{A}$ , $V_{CE} = -5\text{V}$ (*)
Transition Frequency	$f_T$		105		MHz	$I_C = -100\text{mA}$ , $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	$C_{obo}$		31		pF	$V_{CB} = -10\text{V}$ , $f = 1\text{MHz}$ (*)
Delay Time	$t_d$		21		ns	$I_C = -1\text{A}$ , $V_{CC} = -50\text{V}$ , $I_{B1} = -I_{B2} = -100\text{mA}$
Rise Time	$t_r$		18		ns	
Storage Time	$t_s$		680		ns	
Fall Time	$t_f$		75		ns	

### NOTES:

(\*) Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

Typical Characteristics

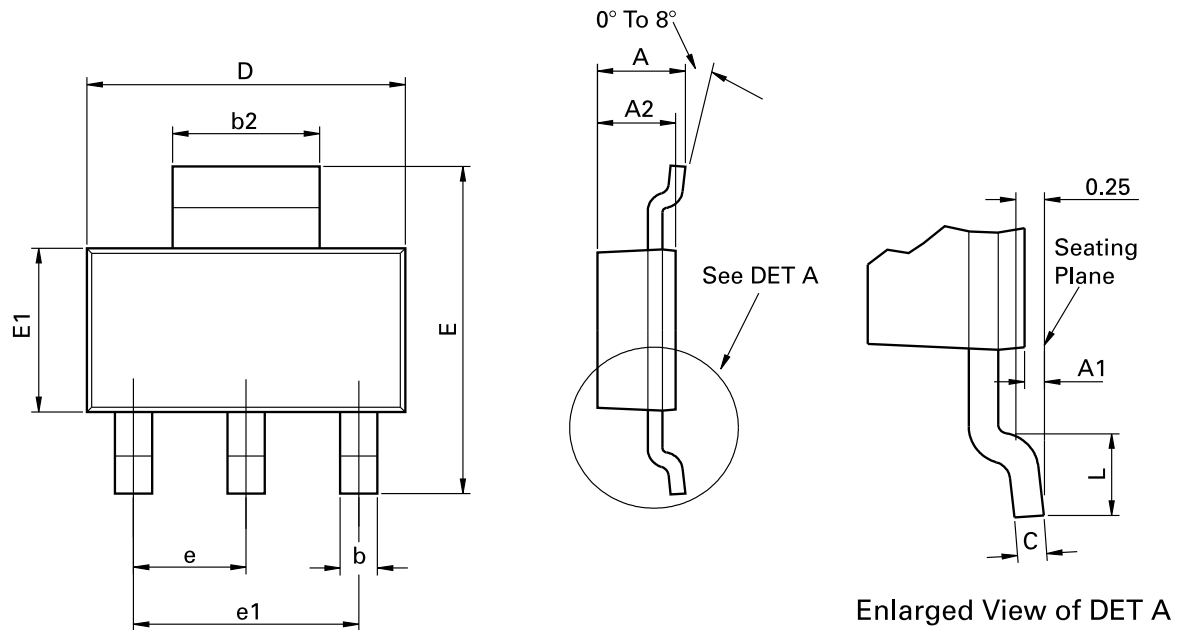


**ZXTP03200BG**

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## Package Information – SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

# ZXTP03200BG

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"Last time buy (LTB)"	Device will be discontinued and last time buy period and delivery is in effect
"Not recommended for new designs"	Device is still in production to support existing designs and production
"Obsolete"	Production has been discontinued

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